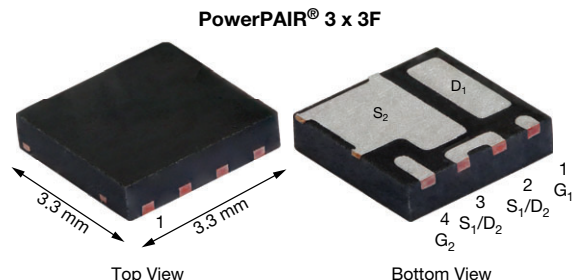


Dual N-Channel 30 V (D-S) MOSFET with Schottky Diode



PRODUCT SUMMARY		
	CHANNEL-1	CHANNEL-2
V_{DS} (V)	30	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00450	0.00184
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00700	0.00257
Q_g typ. (nC)	6.9	19.4
I_D (A) ^a	75	141
Configuration	Dual	

ORDERING INFORMATION	
Package	PowerPAIR 3 x 3F
Lead (Pb)-free and halogen-free	SiZF300DT-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	CHANNEL-1	CHANNEL-2	UNIT
Drain-source voltage	V_{DS}	30	30	V
Gate-source voltage	V_{GS}	+20, -16	+16, -12	
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	75	141	A
	$T_C = 70$ °C	60	113	
	$T_A = 25$ °C	23 ^{b, c}	34 ^{b, c}	
	$T_A = 70$ °C	18 ^{b, c}	27 ^{b, c}	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	150	200	
Continuous source-drain diode current	$T_C = 25$ °C	44	105	
	$T_A = 25$ °C	3.4 ^{b, c}	6.2 ^{b, c}	
Single pulse avalanche current	$L = 0.1$ mH	14	16	
Single pulse avalanche energy	E_{AS}	9.8	12.8	mJ
Maximum power dissipation	$T_C = 25$ °C	48	74	W
	$T_C = 70$ °C	31	47	
	$T_A = 25$ °C	3.8 ^{b, c}	4.3 ^{b, c}	
	$T_A = 70$ °C	2.4 ^{b, c}	2.8 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150		°C
Soldering recommendations (peak temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	CHANNEL-1		CHANNEL-2		UNIT
			TYP.	MAX.	TYP.	MAX.	
Maximum junction-to-ambient ^{b, f}	$t \leq 10$ s	R_{thJA}	26	33	23	29	°C/W
Maximum junction-to-case (source)	Steady state	R_{thJC}	2	2.6	1.3	1.7	

Notes

a. $T_C = 25$ °C

b. Surface mounted on 1" x 1" FR4 board

c. $t = 10$ s

d. See solder profile (www.vishay.com/doc?73257). The PowerPAIR 3 x 3F is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 66 °C/W for channel-1 and 67 °C/W for channel-2

FEATURES

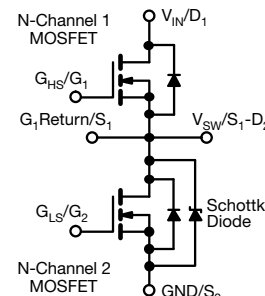
- TrenchFET® Gen IV power MOSFET
- SkyFET® low side MOSFET with integrated Schottky
- 100 % R_g and UIS tested
- Internally connected half-bridge configuration in 3.3 mm-by-3.3 mm footprint
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC





SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30	-	-	V
			Ch-2	30	-	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.1	-	2.2	
			Ch-2	1.0	-	2.2	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 V, -16 V	Ch-1	-	-	± 100	nA
		V _{DS} = 0 V, V _{GS} = +16 V, -12 V	Ch-2	-	-	± 100	
Zero Gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1	-	-	1	μA
			Ch-2	-	30	350	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-1	-	-	5	
			Ch-2	-	150	3000	
On-state drain current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-1	10	-	-	A
			Ch-2	10	-	-	
Drain-source on-state resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A	Ch-1	-	0.00330	0.00450	Ω
		V _{GS} = 10 V, I _D = 10 A	Ch-2	-	0.00160	0.00184	
		V _{GS} = 4.5 V, I _D = 7 A	Ch-1	-	0.00490	0.00700	
		V _{GS} = 4.5 V, I _D = 7 A	Ch-2	-	0.00210	0.00257	
Forward transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 20 A	Ch-1	-	60	-	S
		V _{DS} = 10 V, I _D = 20 A	Ch-2		90	-	
Dynamic ^a							
Input capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	-	1100	-	pF
Output capacitance	C _{oss}		Ch-2	-	3150	-	
			Ch-1	-	530	-	
Reverse transfer capacitance	C _{rss}		Ch-2	-	1550	-	
		Channel-2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1	-	40	-	
C _{rss} /C _{iss} ratio		Ch-2	-	170	-		
		Ch-1	-	0.036	0.072		
		Ch-2	-	0.054	0.108		
		Total gate charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A	Ch-1	-	14.4
Ch-2	-			41	62		
		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A	Ch-1	-	6.9	10.5	
			Ch-2	-	19.4	29	
Gate-source charge	Q _{gs}	Ch-1	-	3.1	-		
		Ch-2	-	7.1	-		
Gate-drain charge	Q _{gd}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A	Ch-1	-	1.5	-	
			Ch-2	-	3.8	-	
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	Ch-1	-	13	-	
			Ch-2	-	40	-	
Gate resistance	R _g	f = 1 MHz	Ch-1	0.14	0.7	1.4	Ω
			Ch-2	0.12	0.62	1.2	
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	17	35	ns
			Ch-2	-	25	50	
Rise time	t _r		Ch-1	-	40	80	
			Ch-2	-	53	110	
Turn-off delay time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1	-	23	45	
			Ch-2	-	30	60	
Fall time	t _f	Ch-1	-	7	15		
		Ch-2	-	12	25		
Turn-on delay time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	11	20	
			Ch-2	-	13	25	
Rise time	t _r		Ch-1	-	5	10	
			Ch-2	-	20	40	
Turn-off delay time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1	-	23	45	
			Ch-2	-	32	65	
Fall time	t _f	Ch-1	-	5	10		
		Ch-2	-	6	15		

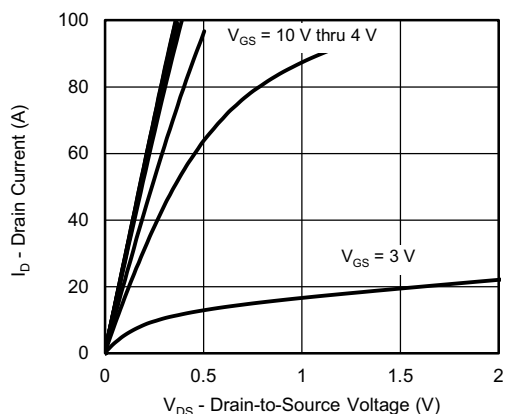
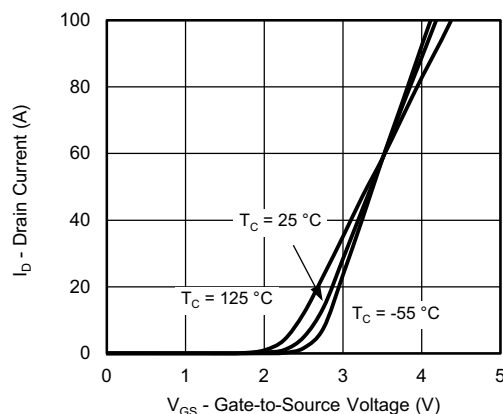
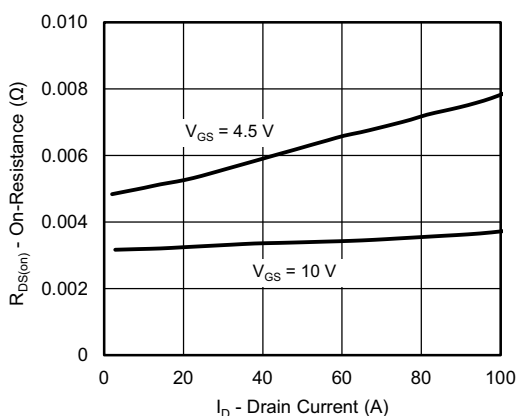
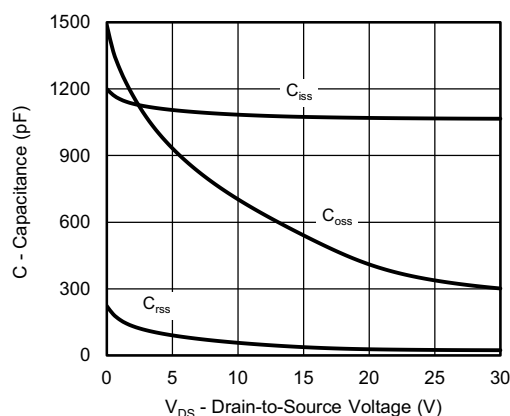
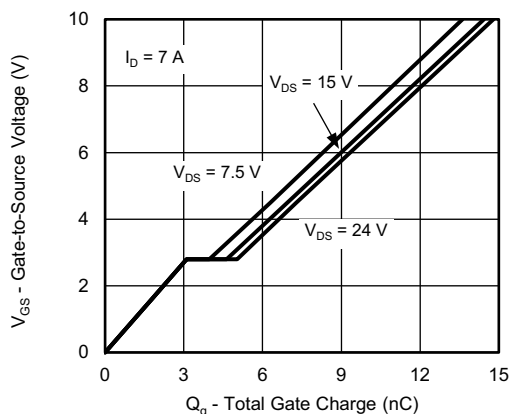
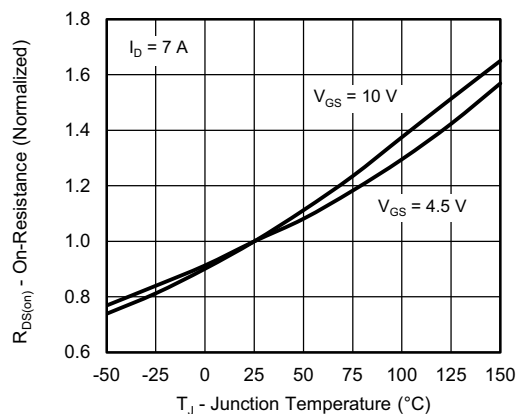


SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	Ch-1	-	-	44	A
			Ch-2	-	-	105	
Pulse diode forward current ^a	I _{SM}		Ch-1	-	-	150	
			Ch-2	-	-	200	
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	Ch-1	-	0.75	1.1	V
		I _S = 5 A, V _{GS} = 0 V	Ch-2	-	0.44	0.7	
Body diode reverse recovery time	t _{rr}	Channel-1 I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	36	75	ns
			Ch-2	-	46	90	
Body diode reverse recovery charge	Q _{rr}		Ch-1	-	26	55	nC
			Ch-2	-	40	80	
Reverse recovery fall time	t _a	Channel-2 I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	Ch-1	-	16	-	ns
			Ch-2	-	18	-	
Reverse recovery rise time	t _b		Ch-1	-	20	-	
			Ch-2	-	28	-	

Notes

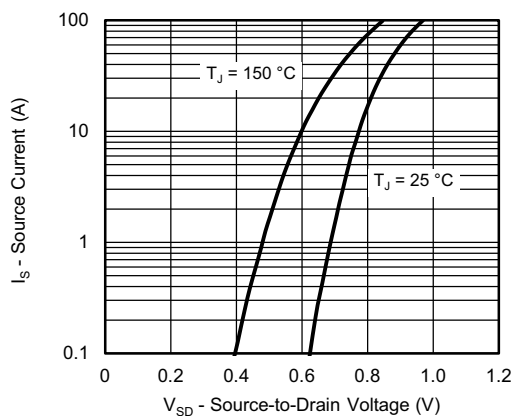
- a. Guaranteed by design, not subject to production testing
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

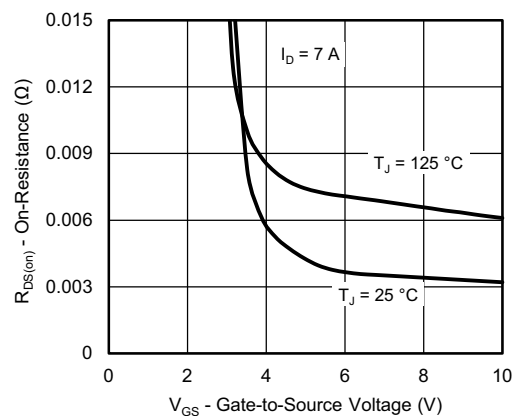
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



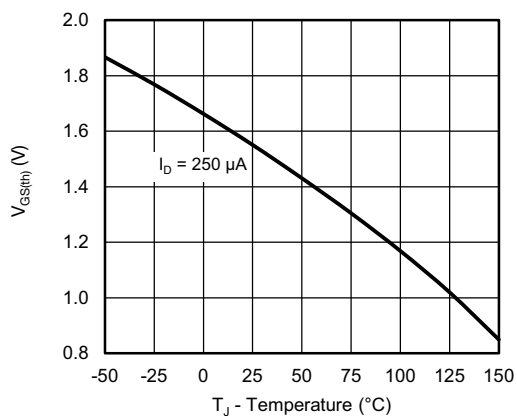
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



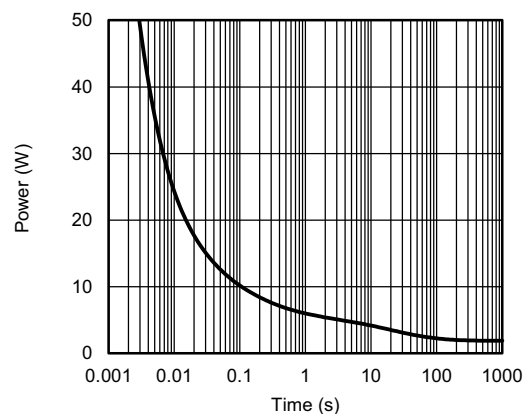
Source-Drain Diode Forward Voltage



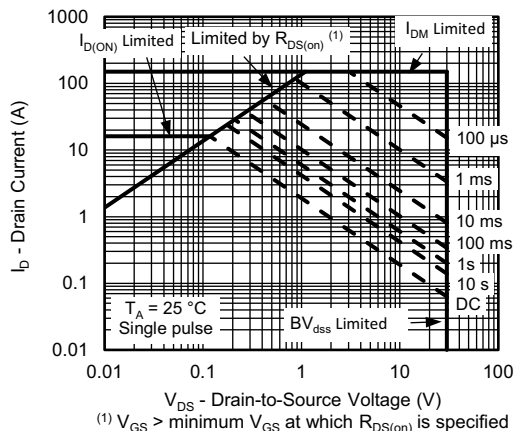
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



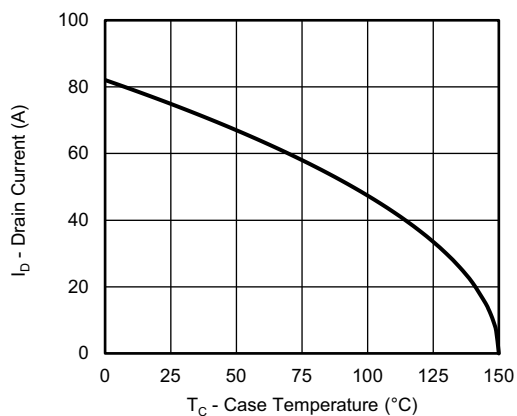
Single Pulse Power, Junction-to-Ambient



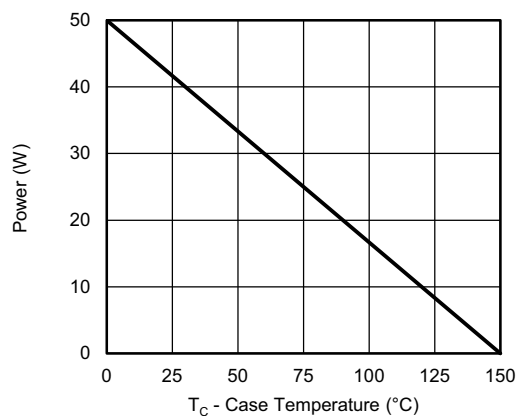
Safe Operating Area, Junction-to-Ambient



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



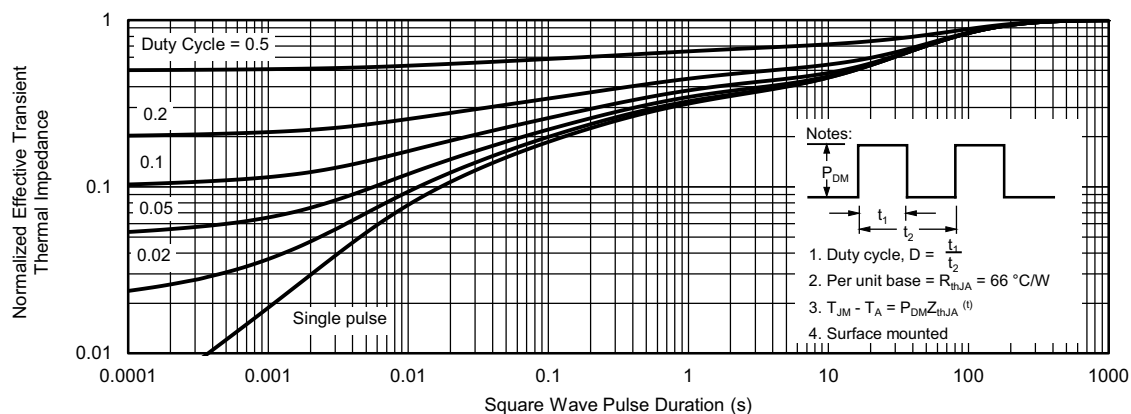
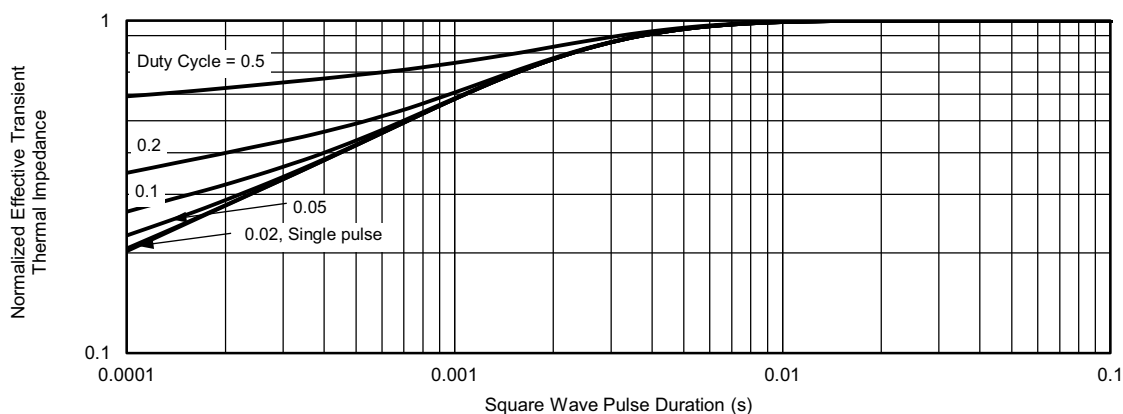
Current Derating ^a

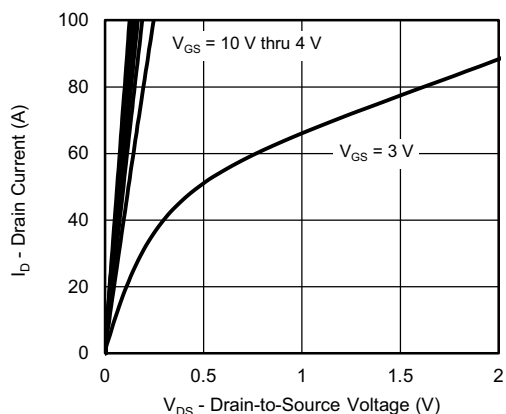
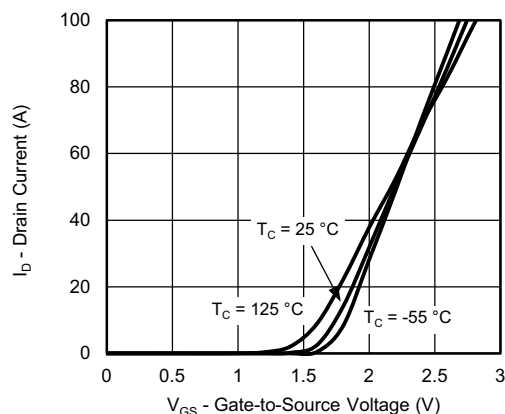
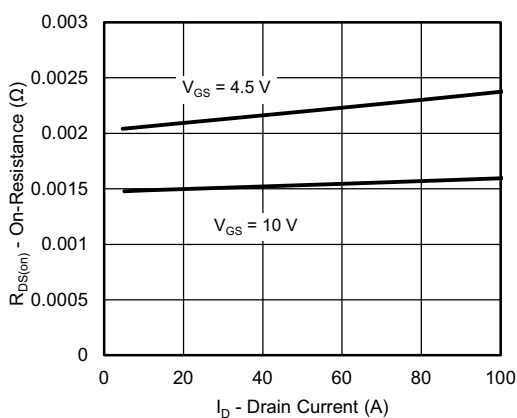
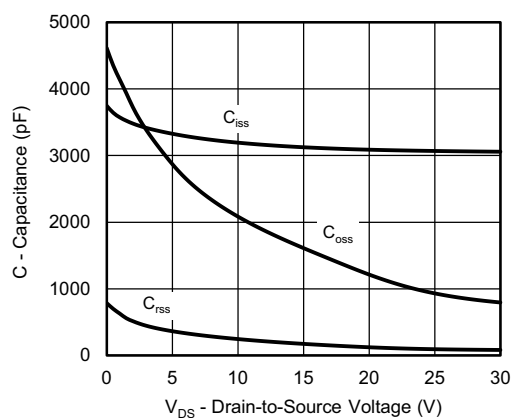
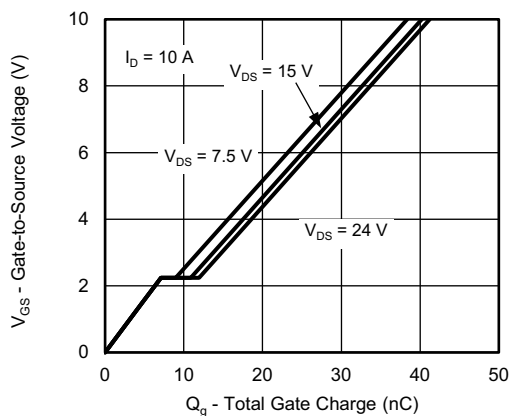
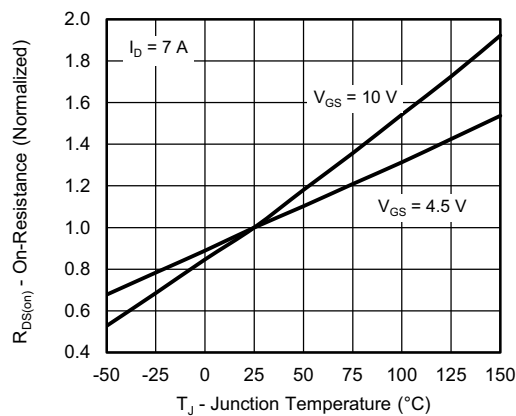


Power, Junction-to-Case

Note

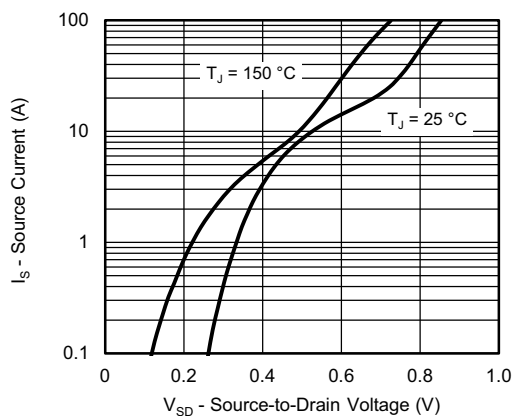
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

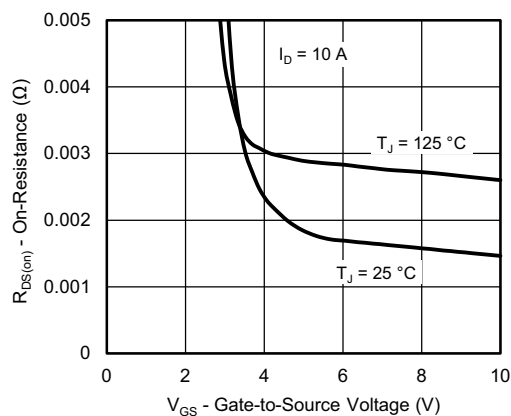
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



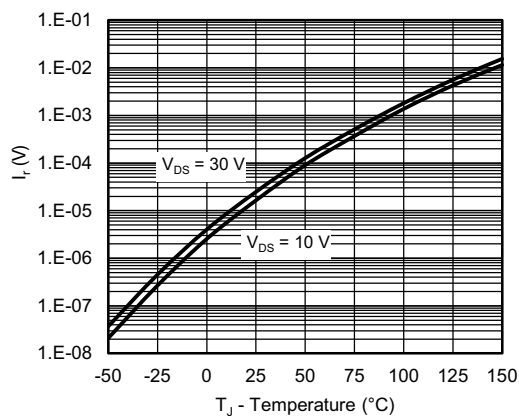
CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



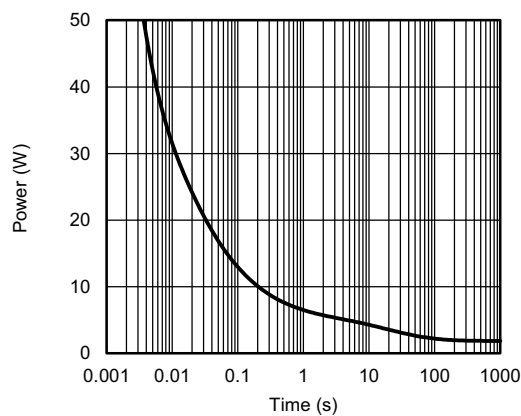
Source-Drain Diode Forward Voltage



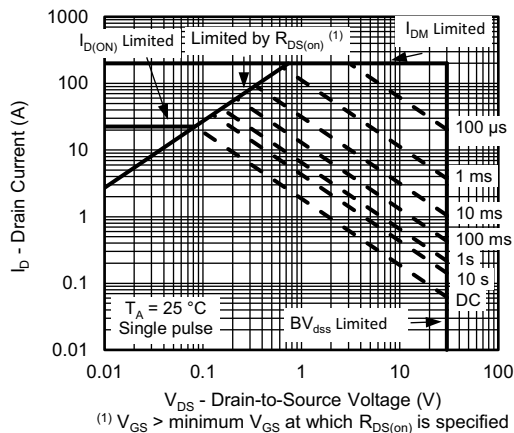
On-Resistance vs. Gate-to-Source Voltage



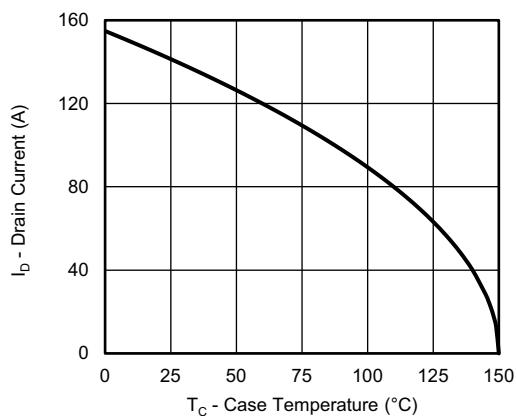
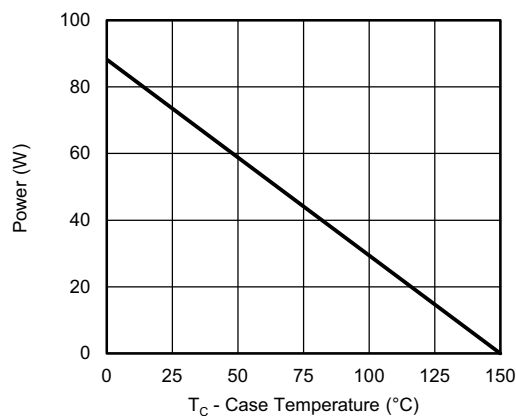
Reverse Current (Schottky)



Single Pulse Power, Junction-to-Ambient



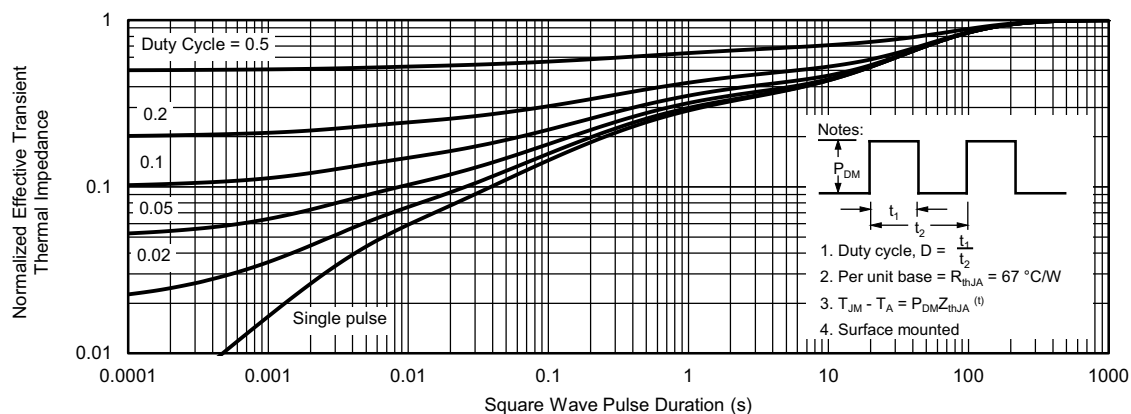
Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case
Note

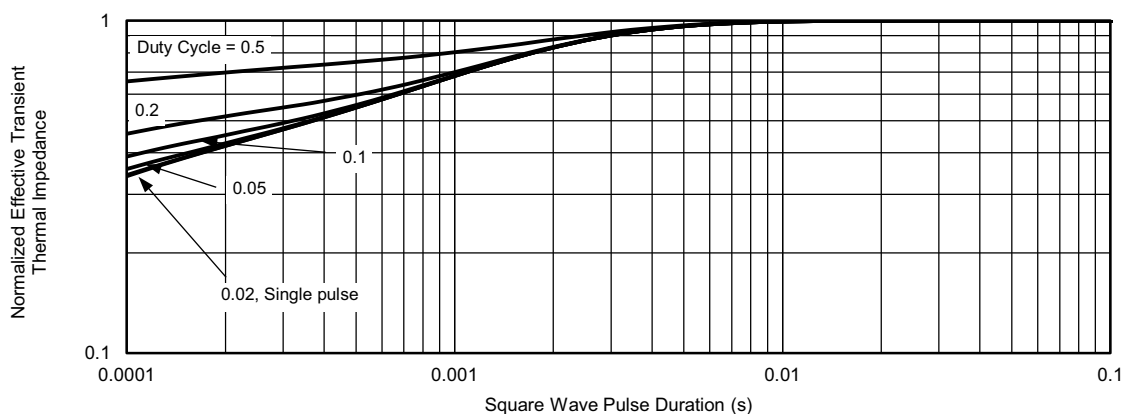
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



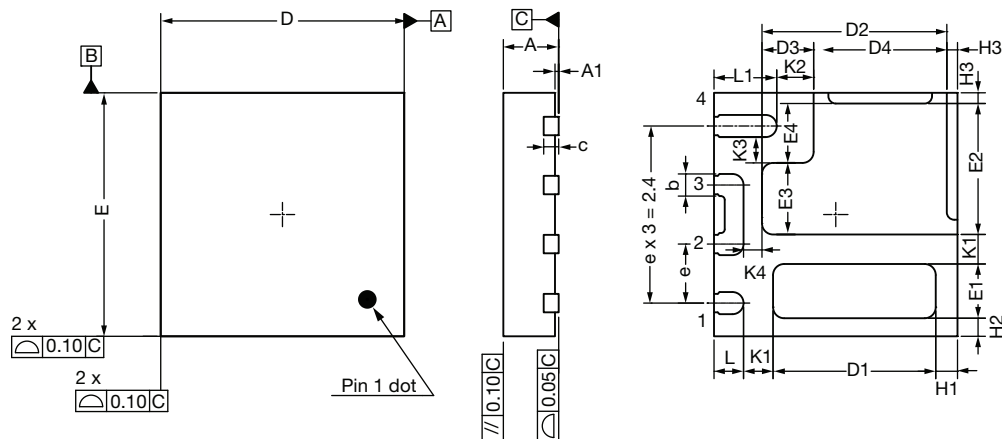
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76288.

PowerPAIR® 3 x 3F Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.20 ref.			0.008 ref.		
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.20	2.25	0.085	0.087	0.089
D2	2.45	2.50	2.55	0.096	0.098	0.100
D3	0.65	0.70	0.75	0.026	0.028	0.030
D4	1.75	1.80	1.85	0.069	0.071	0.073
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	0.69	0.74	0.79	0.027	0.029	0.031
E2	1.73	1.78	1.93	0.068	0.070	0.072
E3	0.92	0.97	1.02	0.036	0.038	0.040
E4	0.76	0.81	0.86	0.030	0.032	0.034
e	0.80 BSC			0.031 BSC		
K1	0.40 ref.			0.016 ref.		
K2	0.50 ref.			0.020 ref.		
K3	0.35 ref.			0.014 ref.		
K4	0.25 ref.			0.010 ref.		
H1	0.30 ref.			0.012 ref.		
H2	0.25 ref.			0.010 ref.		
H3	0.15 ref.			0.006 ref.		
L	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.80	0.85	0.90	0.031	0.033	0.035

T18-0135-Rev. A, 02-Apr-18
DWG: 6065

Notes

- Use millimeters as the primary measurement
- Dimensioning and tolerances conform to ASME Y14.5M - 1994
- N is the number of terminals; Nd is the number of terminals in X-direction; Ne is the number of terminals in Y-direction
- Dimension b applies to plated terminal and is measured between 0.20 mm and 0.25 mm from terminal tip
- The pin # 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- Exact shape and size of this features is optional
- Package warpage max. 0.08 mm
- Applied only for terminals



Disclaimer

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